NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI PTB32005X** is Designed for Common Base General purpose amplifier Applications up to 4.2 GHz.

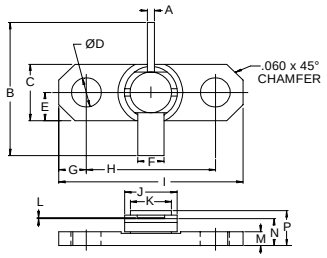
FEATURES INCLUDE:

- Diffused Emitter Ballasting Resistor
- Hermetic Flange Package
- Gold Metelization

MAXIMUM RATINGS

I_C	750 mA
V_{CBO}	40 V
P_{DISS}	8.7 W @ T_C = 75 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	10.5 °C/W

PACKAGE STYLE .250 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 3.0 mA			40			V
BV_{CES}	I_C = 10 mA			40			V
I_{CBO}	V_{CE} = 24 V					30	µA
I_{EBO}	V_{EB} = 1.5 V					0.6	µA
C_{cb}	V_{CB} = 24 V	V_{EB} = 1.5 V	f = 1.0 MHz		3.8		pF
C_{ce}	V_{CB} = 24 V	V_{EB} = 1.5 V	f = 1.0 MHz		0.9		pF
P_{OUT}	V_{CC} = 24 V		f = 3.0 GHz	4.5			W
η_C				35			%
G_P				8.0			dB

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Specifications are subject to change without notice.